Supplementary Information

Enhanced magnetic anisotropy and high hole mobility in magnetic semiconductor $Ga_{1-x-y}Fe_xNi_ySb$

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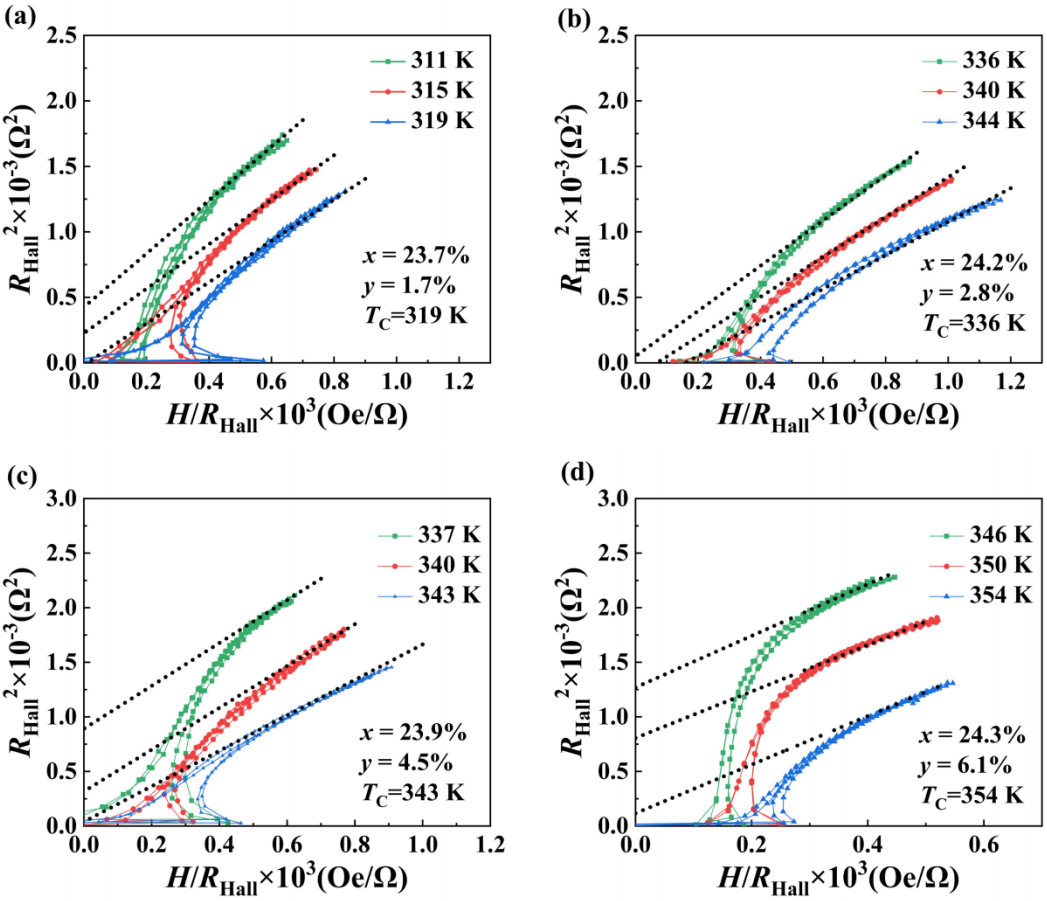
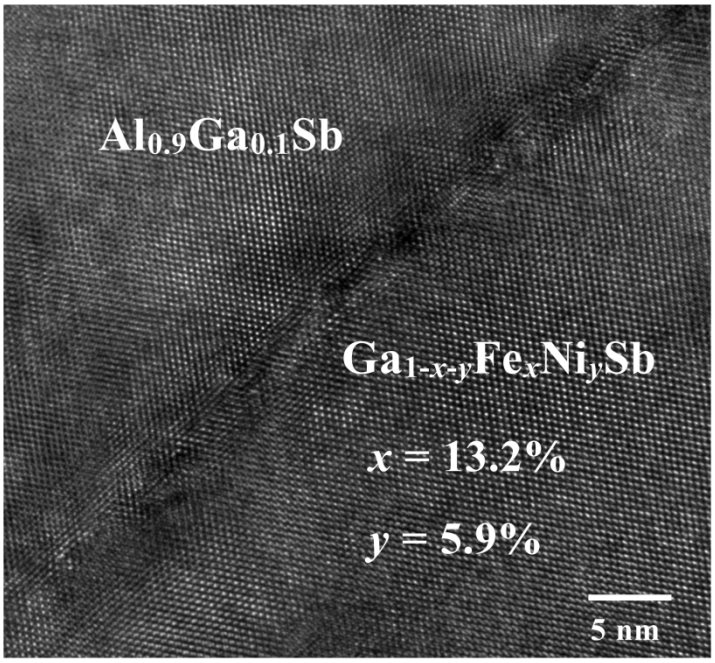
Supplementary Figures



Supplementary Figure S1. a-d, Arrott plots of the R_{Hall}-H characteristics of samples B1-B4 (x≈24%, y=1.7-6.1%).



Supplementary Figure S2. A clear STEM image of sample S1 with low impurity concentration (x=13.2%, y=5.9%). When Fe concentration is over 20%, the ferromagnetism of $Ga_{1-x-y}Fe_xNi_ySb$ existed at 300 K would make great influence on the STEM images. Thus, a clear STEM image could only be obtained at the films with low doping concentration.